

isc Silicon NPN Power Transistor
2SC2098
DESCRIPTION

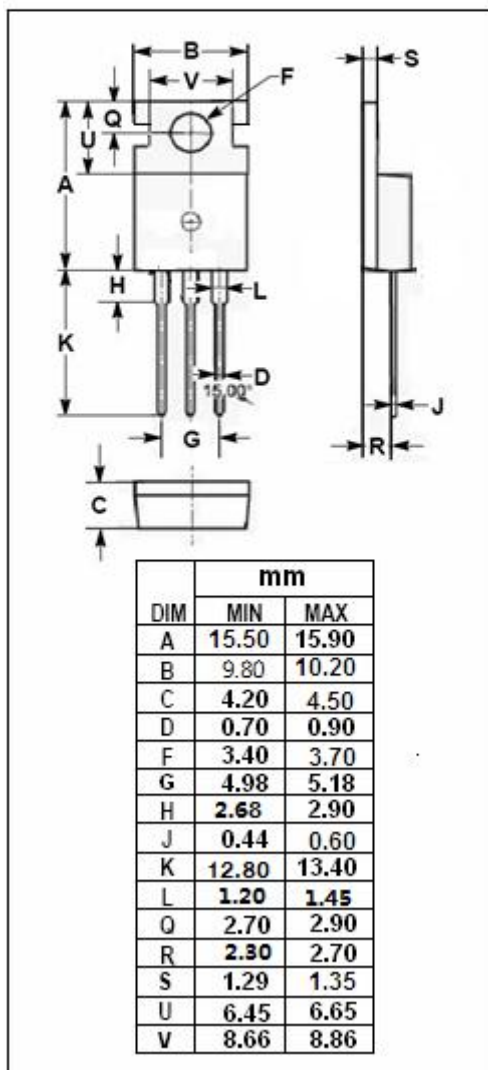
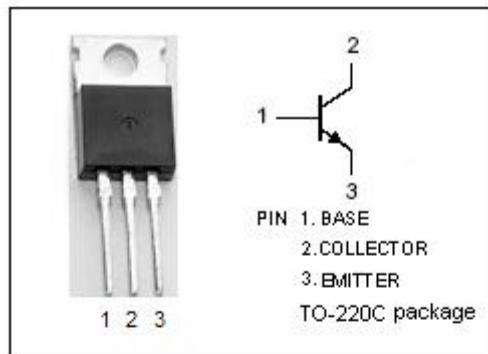
- Silicon NPN epitaxial planar
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- The 2SC2098 is designed for 25=50MHz AF power amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	70	V
V _{CEO}	Collector-Emitter Voltage	70	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current-Continuous	6	A
P _C	Total Power Dissipation @ T _C =25°C	25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _c = 25mA; I _b = 0	70			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 70V; I _E = 0			1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			1	mA
h _{FE}	DC Current Gain	I _c = 4A; V _{CE} = 5V	20		100	

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